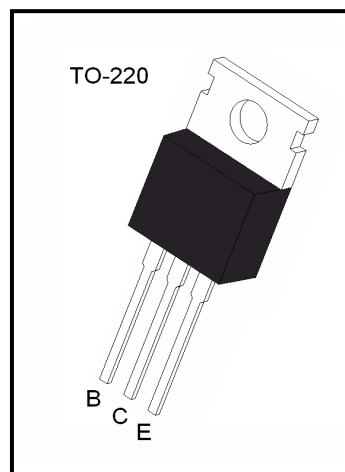


NPN Epitaxial Silicon Transistor**Medium Power Linear Switching Applications**

- Complementary to TIP42/42A/42B/42C

Absolute Maximum Rating (Ta=25℃)

Parameter	Symbol	Value				Unit
		TIP41	TIP41A	TIP41B	TIP41C	
Collector-Base Voltage	V _{CBO}	40	60	80	100	V
Collector-Emitter Voltage	V _{CEO}	40	60	80	100	V
Emitter-Base Voltage	V _{EBO}	5				V
Collector Current(DC)	I _C	3				A
Collector Dissipation	Ta =25 ℃	2				W
	Tc =25 ℃					
Junction Temperature	T _j	150				℃
Storage Temperature	T _{stg}	-65~150				℃

**Electrical Characteristics (Ta=25℃)**

Parameter		Symbol	Conditions	Value			Unit
				Min	Typ	Max	
Collector-Emitter Sustaining Voltage	TIP41 TIP41A TIP41B TIP41C	V _{CEO(sus)}	I _C = 30mA, I _B = 0	40 60 80 100			V
Collector cut-off current	TIP41 TIP41A TIP41B TIP41C	I _{CBO}	V _{CE} =40V, I _E = 0 V _{CE} = 60V, I _E = 0 V _{CE} = 80V, I _E = 0 V _{CE} =100V, I _E = 0			200	μA
Collector cut-off current	TIP41/41A TIP41B/41C	I _{CEO}	V _{CB} =30V, I _E = 0 V _{CB} = 60V, I _E = 0			0.3	mA
Emitter cut-off current			V _{EB} = 5V, I _C = 0			1	mA
* DC current gain		h _{FE}	V _{CE} = 4V, I _C = 1A V _{CE} = 4V, I _C = 3A	25 10		50	
*Collector-emitter saturation voltage		V _{CE(sat)}	I _C = 3A, I _B =375mA			1.2	V
* Base-Emitter ON Voltage		V _{BE (on)}	V _{CE} = 4V, I _C = 3A			1.8	V
Current Gain Bandwidth Product		f _T	V _{CE} =10V, I _C =500mA	3.0			MHz

* Pulse Test : PW≤300μs, Duty cycle≤2%